

N-channel TrenchPLUS logic level FET Rev. 02 — 21 June 2010

Product data sheet

Product profile 1.

1.1 General description

N-channel enhancement mode field-effect power transistor in SOT427. Device is manufactured using Nexperia High-Performance TrenchPLUS technology, featuring very low on-state resistance, integrated current sensing transistors and over temperature protection diodes.

1.2 Features and benefits

AEC-Q101 compliant

Low conduction losses due to low on-state resistance

Power distribution

Solenoid drivers

1.3 Applications

- Lamp switching
- Motor drive systems

1.4 Quick reference data

Table 1.	Quick reference da	ata				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 V; I_D = 25 A;$ $T_j = 25 °C; see Figure 13;$ see Figure 12	-	8.5	10	mΩ
I _D /I _{sense}	ratio of drain current to sense current	T _j = 25 °C; V _{GS} = 5 V; see <u>Figure 14</u>	8094	8993	9892	A/A
V _{(BR)DSS}	drain-source breakdown voltage	$ I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \\ T_j = 25 \ ^\circ\text{C} $	65	-	-	V



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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	IS	current sense	mb	
3	А	anode		
4	D	drain	ii	
5	K	cathode		IS KS S C
6	KS	Kelvin source		003aad829
7	S	source	SOT427 (D2PAK)	
mb	D	mb		

3. Ordering information

Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
BUK9C10-65BIT	D2PAK	plastic single-ended surface-mounted package (D2PAK); 7 leads (one lead cropped)	SOT427

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

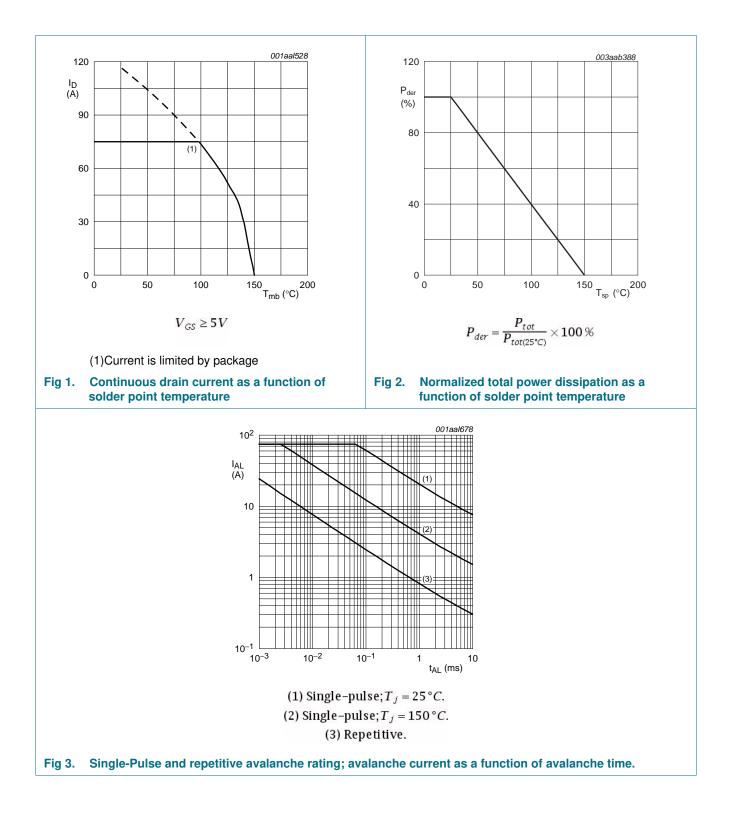
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	-	65	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega; 25 \text{ °C} \le T_j \le 150 \text{ °C}$		-	-	65	V
V _{GS}	gate-source voltage			-15	-	15	V
I _D	drain current	$V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{1}$	<u>[1]</u>	-	-	75	А
		V_{GS} = 5 V; T_{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	-	60	А
I _{DM}	peak drain current	T_{mb} = 25 °C; single pulse; $t_p \le 10 \ \mu$ s; see Figure 4		-	-	346	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	171	W
T _{stg}	storage temperature			-55	-	150	°C
Tj	junction temperature			-55	-	150	°C
$V_{\text{isol}(\text{FET-TSD})}$	FET to temperature sense diode isolation voltage			-	-	100	V
Source-drain d	liode						
I _S	source current	T _{mb} = 25 °C	<u>[1]</u>	-	-	75	А
I _{SM}	peak source current	single pulse; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	-	346	А
Avalanche rug	gedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 75 \text{ A}; V_{sup} = 65 \text{ V}; V_{GS} = 5 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{unclamped}; \text{see } \underline{\text{Figure 3}} \end{split}$	<u>[2][3]</u>	-	-	0.214	J
Electrostatic d	ischarge						
V _{ESD}	electrostatic discharge	HBM; C = 100 pF; R = 1.5 k Ω ; all pins		-	-	0.15	kV
	voltage	HBM; C = 100 pF; R = $1.5 \text{ k}\Omega$; pin 4 to pin 7		-	-	4	kV

[1] Current is limited by package

[2] Single-pulse avalanche rating limited by maximum junction temperature of 150 °C.

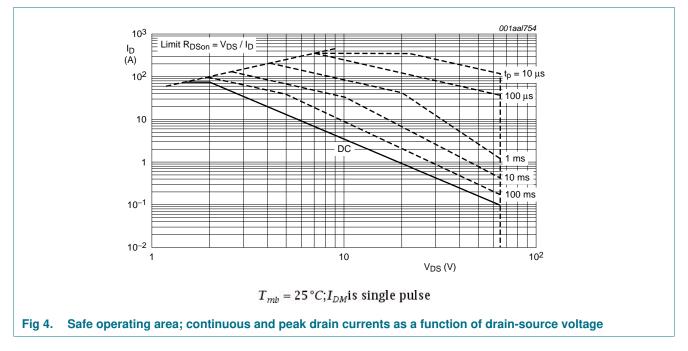
[3] Refer to application note AN10273 for further information.

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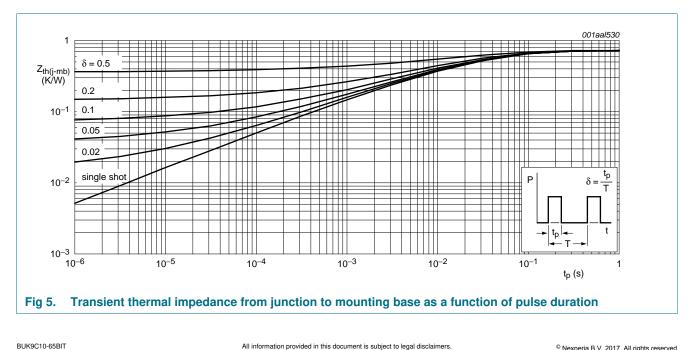
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Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	-	0.73	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	61	-	K/W



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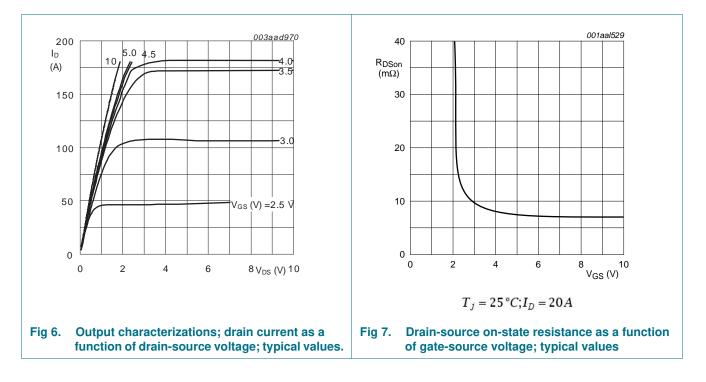
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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	65	-	-	V
	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	59	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10; see Figure 11	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 52 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	3	μA
		V _{DS} = 52 V; V _{GS} = 0 V; T _j = 150 °C	-	-	125	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 15 V; T_j = 25 \text{ °C}$	-	2	300	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; see Figure 12; see Figure 13	-	-	11	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13; see Figure 12	-	8.5	10	mΩ
		$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 150 \text{ °C};$ see Figure 13; see Figure 12	-	-	20	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 13; see Figure 12	-	-	8.3	mΩ
I _D /I _{sense}	ratio of drain current to sense current	V_{GS} = 5 V; T_j = 25 °C; see <u>Figure 14</u>	8094	8993	9892	A/A
$S_{F(TSD)}$	temperature sense diode temperature coefficient	I _F = 250 μA; 25 °C ≤ T _j ≤ 150 °C; see <u>Figure 15</u>	-5.4	-5.7	-6	mV/K
$V_{F(TSD)}$	temperature sense diode forward voltage	$I_F = 250 \ \mu\text{A}; T_j = 25 \ ^\circ\text{C}; \text{see} \ \underline{Figure \ 15}$	2.855	2.9	2.945	V
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 52 \text{ V}; V_{GS} = 5 \text{ V};$	-	59.6	-	nC
Q _{GS}	gate-source charge	see Figure 16	-	10.4	-	nC
Q _{GD}	gate-drain charge		-	21.6	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	4170	-	pF
Coss	output capacitance	T _j = 25 °C; see <u>Figure 17</u>	-	521	-	pF
C _{rss}	reverse transfer capacitance		-	194	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.5 Ω ; V_{GS} = 5 V;	-	40	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	113	-	ns
t _{d(off)}	turn-off delay time		-	193	-	ns
t _f	fall time		-	108	-	ns
L _D	internal drain inductance	from pin to center of die	-	0.9	-	nH

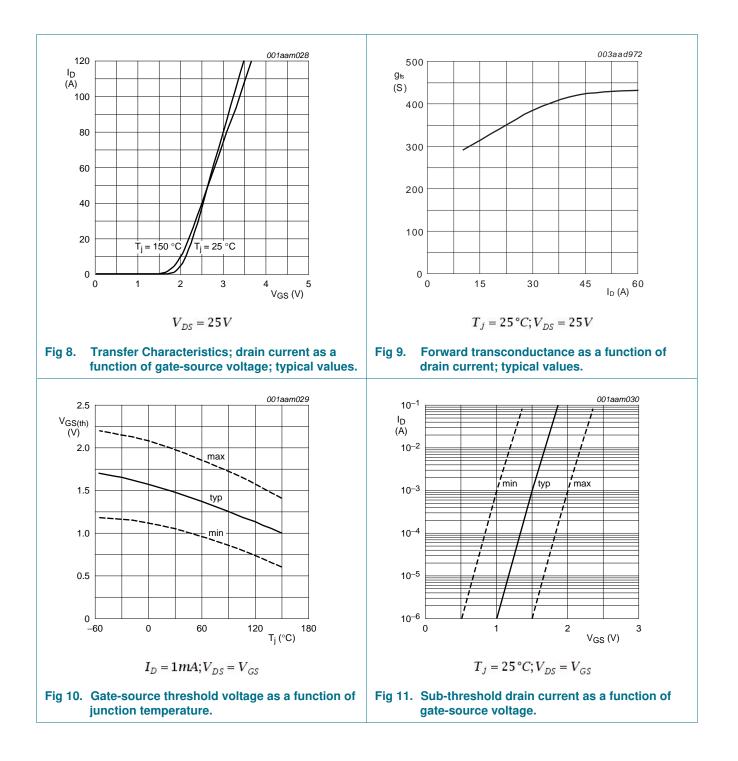
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Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
L _S	internal source inductance	from source lead to source bonding pad	-	2	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 18</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s;$	-	51	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}$	-	0.12	-	nC



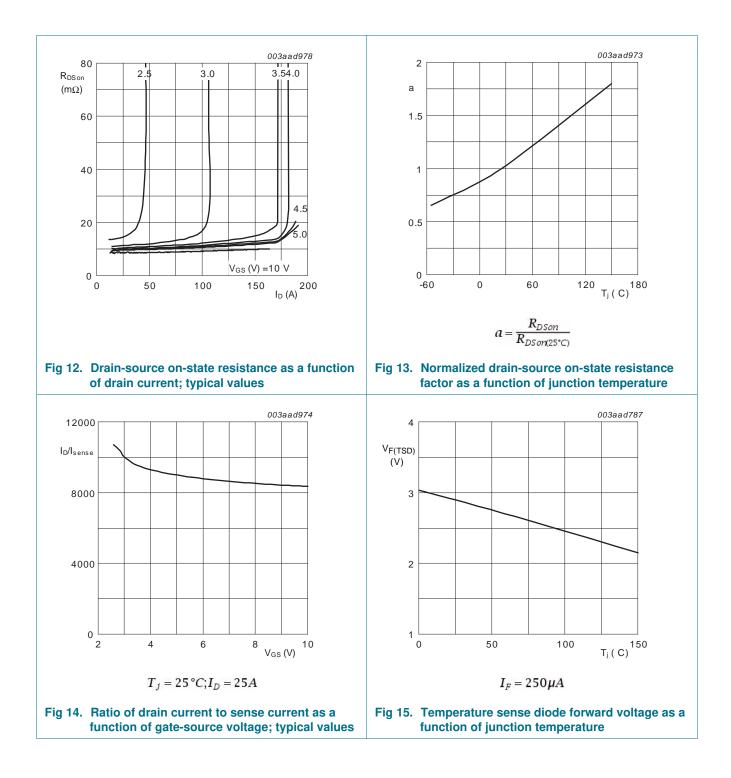
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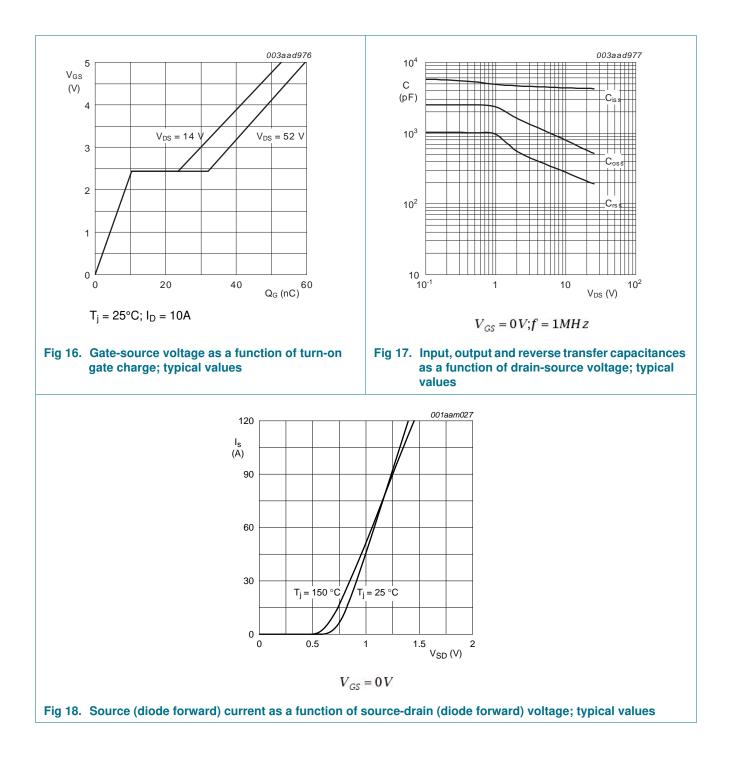


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7. Package outline

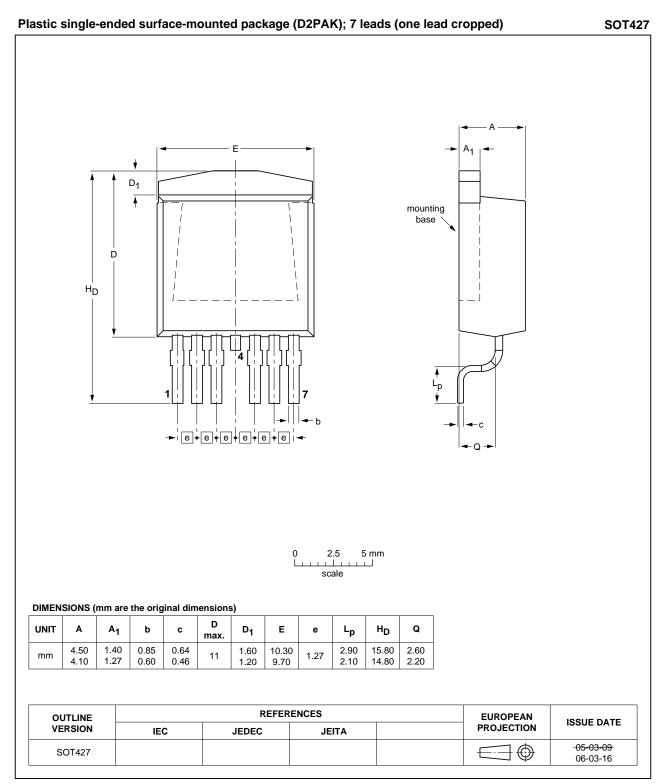


Fig 19. Package outline SOT427 (D2PAK)

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8. Revision history

Table 7. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9C10-65BIT v.2	20100621	Product data sheet	-	BUK9C10-65BIT v.1
Modifications:	 Status char 	nged from preliminary to pro	oduct.	
BUK9C10-65BIT v.1	20100531	Preliminary data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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